

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
60V	2Ω@10V	100mA
	2.5Ω@4.5V	



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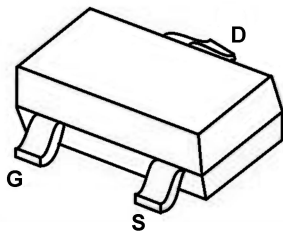
Feature

- High power and current handing capability
- Surface mount package
- ESD protected 2KV

Application

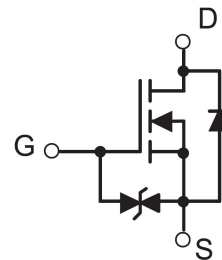
- Battery Switch
- DC/DC Converter

Package

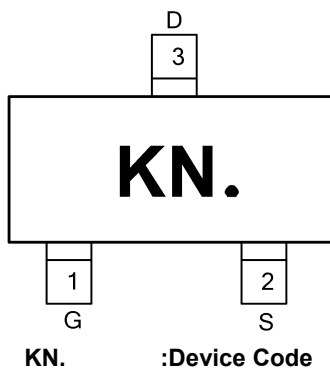


SOT-523

Circuit diagram



Marking



Order Information

Device	Package	Unit/Tape
2SK3019A	SOT-523	3000

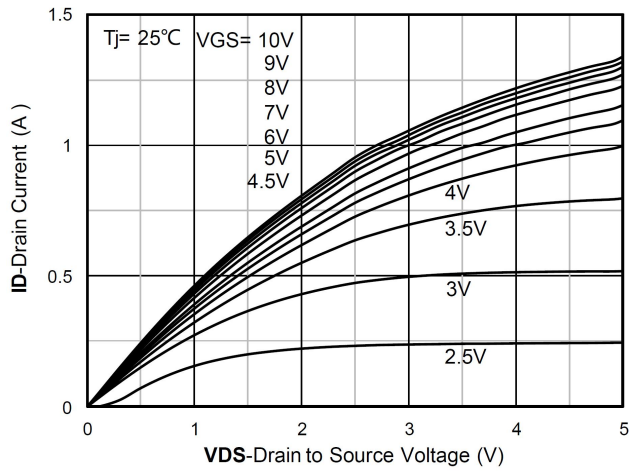
Absolute maximum ratings (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	60	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current	I _D	100	mA
Pulse Drain Current Tested	I _{DM}	400	mA
Power Dissipation	P _D	150	mW
Thermal Resistance Junction-to-Ambient	R _{θJA}	833	°C/W
Storage Temperature Range	T _{STG}	-55 to 150	°C
Operating Junction Temperature Range	T _J	-55 to 150	°C

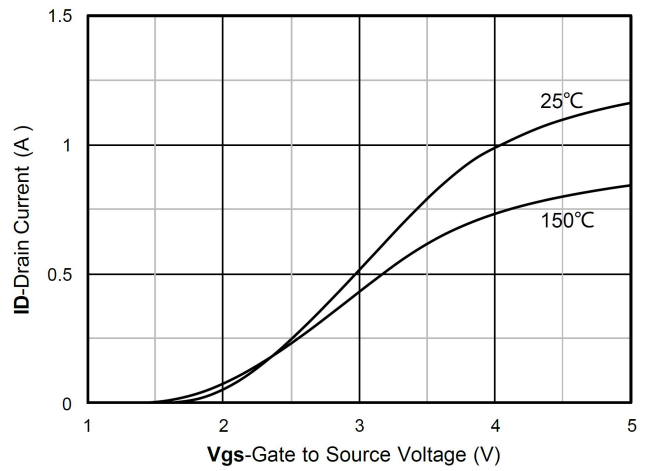
Electrical characteristics (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V , I _D =250μA	60	-	-	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =48V , V _{GS} =0V	-	-	1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V , V _{DS} =0V	-	-	±10	uA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.7	1	1.45	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =200mA	-	2	5	Ω
		V _{GS} =4.5V, I _D =100mA	-	2.5	8	
Dynamic characteristics						
Input Capacitance	C _{iss}	V _{DS} =25V , V _{GS} =0V , f=1MHz	-	12	-	pF
Output Capacitance	C _{oss}		-	6	-	
Reverse Transfer Capacitance	C _{rss}		-	2.5	-	
Total Gate Charge	Q _g	V _{DS} =10V , V _{GS} =15V , I _D =1A	-	1.34	-	nC
Gate-Source Charge	Q _{gs}		-	0.29	-	
Gate-Drain Charge	Q _{gd}		-	0.2	-	
Switching Characteristics						
Turn-On Delay Time	t _{d(on)}	V _{DD} =15V V _{GS} =10V , R _G =2.3Ω , I _D =1A	-	5	-	nS
Turn-On Rise Time	t _r		-	18	-	
Turn-Off Delay Time	t _{d(off)}		-	8	-	
Turn-Off Fall Time	t _f		-	14	-	
Source-Drain Diode characteristics						
Diode Forward Voltage	V _{SD}	V _{GS} =0V , I _S =1A , T _J =25°C	-	-	1.2	V

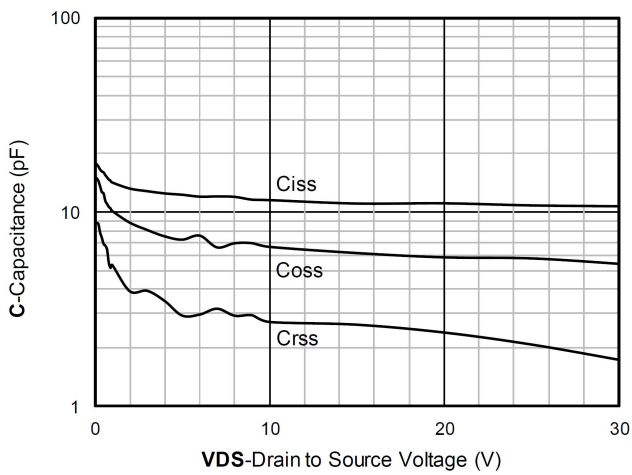
Typical Characteristics



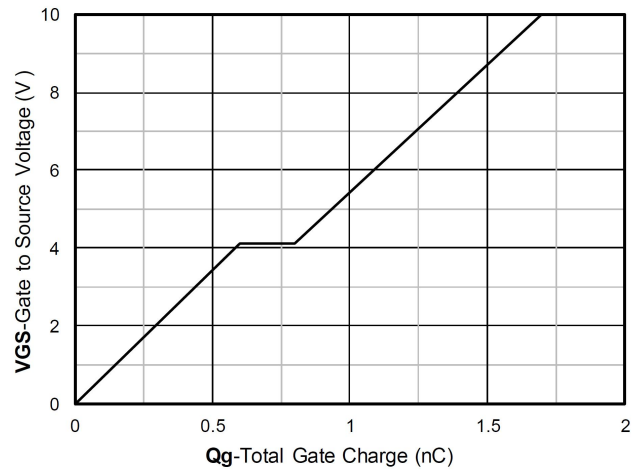
Output Characteristics



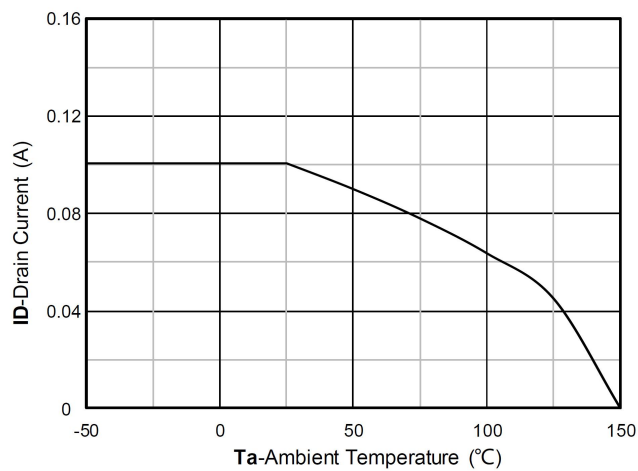
Transfer Characteristics



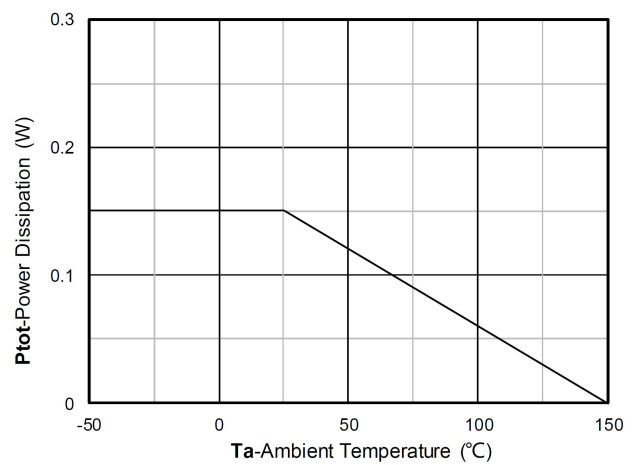
Capacitance Characteristics



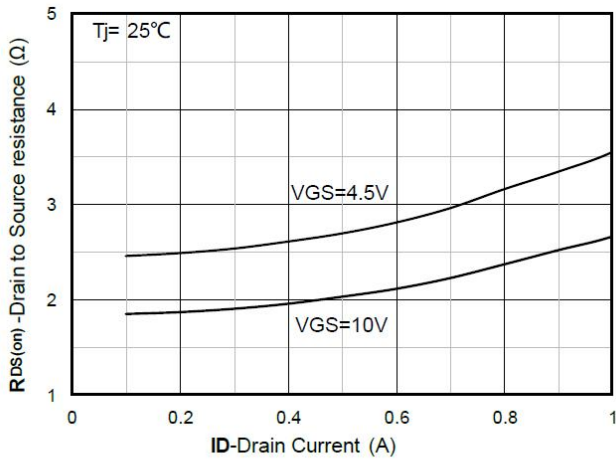
Gate Charge



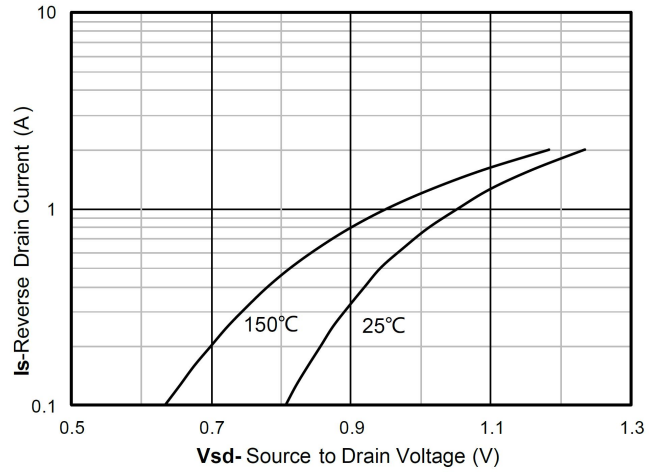
Current dissipation



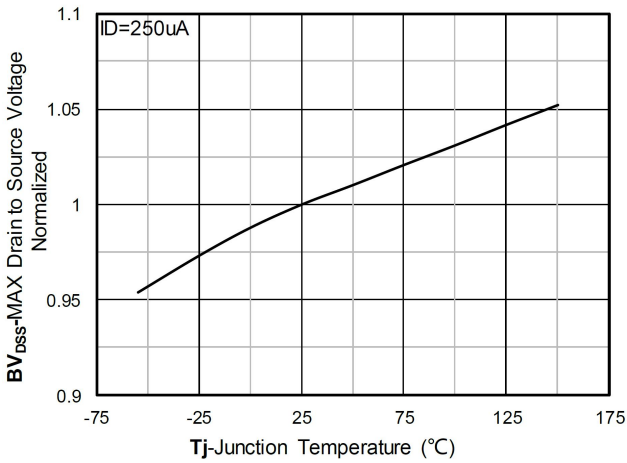
Power dissipation



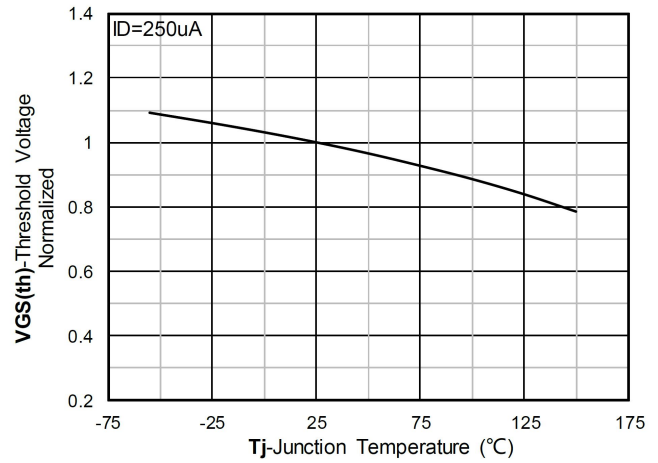
RDS(on) VS Drain Current



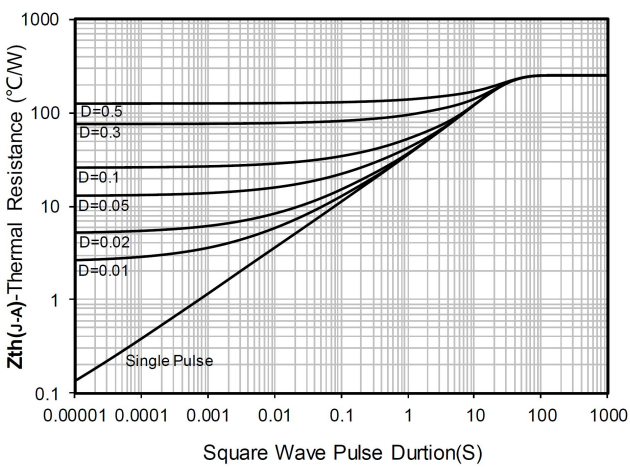
Forward characteristics of reverse diode



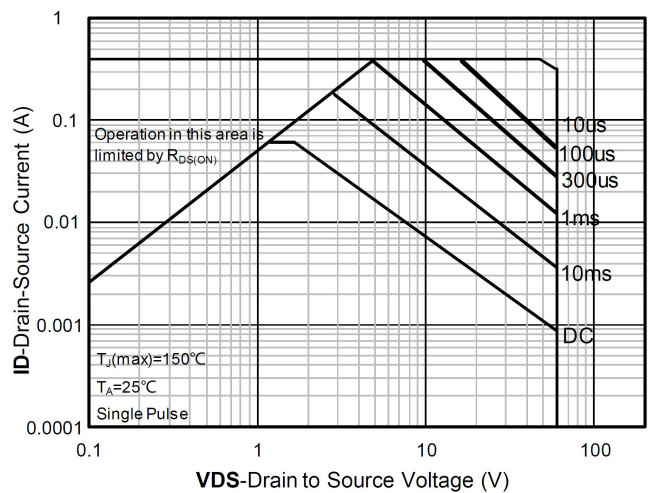
Normalized breakdown voltage



Normalized Threshold voltage

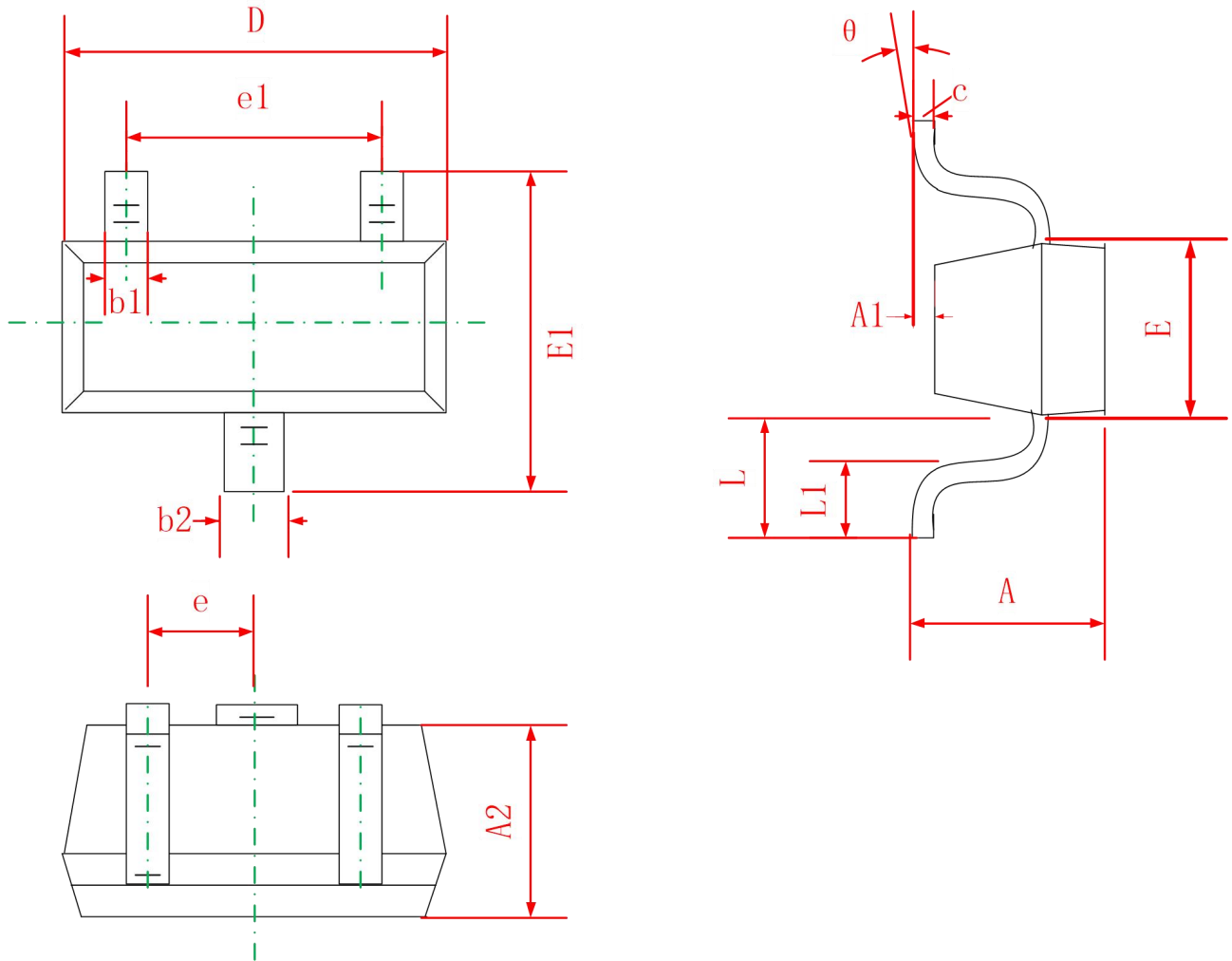


Maximum Transient Thermal Impedance



Safe Operation Area

SOT-523 Package Information



Symbol	Dimensions In Millimeters	
	Min	Max
A	0.700	0.900
A1	0.000	0.100
A2	0.700	0.800
b1	0.150	0.250
b2	0.250	0.350
C	0.100	0.200
D	1.500	1.700
E	0.700	0.900
E1	1.450	1.750
e	0.500 TYP	
e1	0.900	1.100
L	0.400 REF	
L1	0.260	0.460
θ	0°	8°